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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	0.25	-	5	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2—T1
2	G	gate		G sym051
3	T1	main terminal 1	TO-92 (SOT54)	sylnost

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA2008-800D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 70 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	9	А
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	9.9	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.41	A²s
dl _T /dt	rate of rise of on-state current	I _G = 20 mA	-	100	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

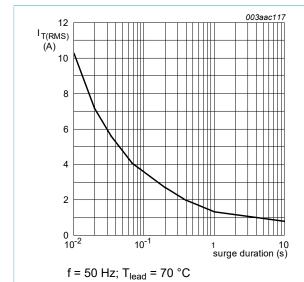


Fig. 1. RMS on-state current as a function of surge duration; maximum values

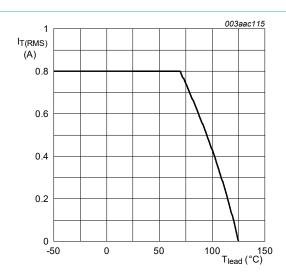


Fig. 2. RMS on-state current as a function of lead temperature; maximum values

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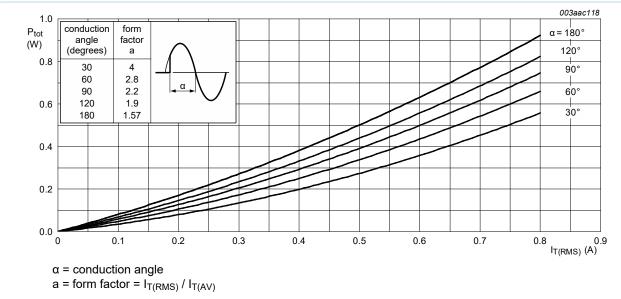


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

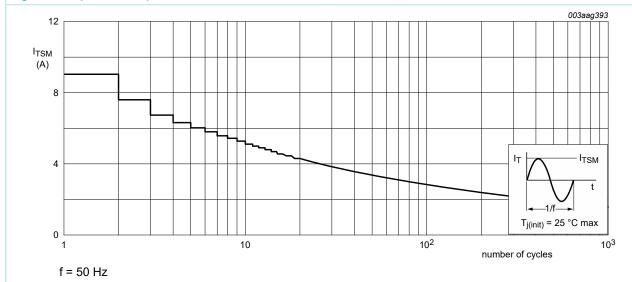
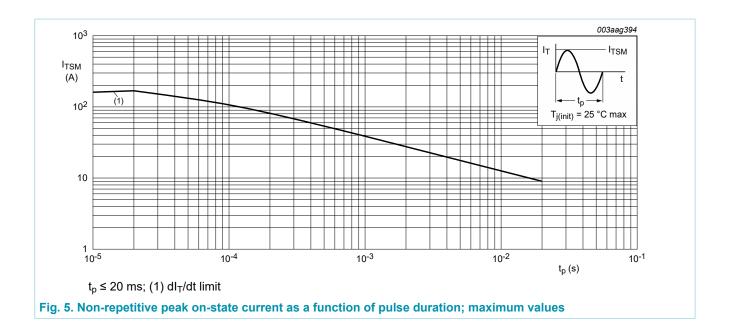


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

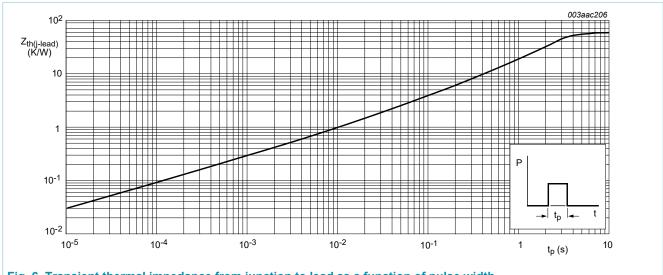


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

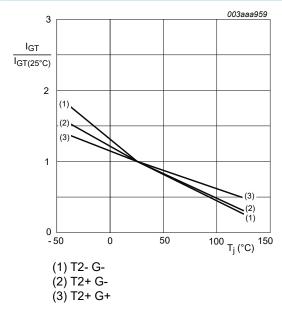
9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	0.25	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	0.25	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	0.25	-	5	mA
I _L latching current	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.9	1.5	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics		'			,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 0.8 A; dV_{com}/dt = 10 V/ μ s; gate open circuit	0.5	-	-	A/ms

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junction temperature

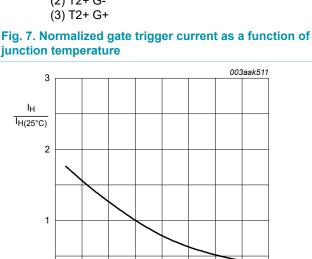


Fig. 9. Normalized holding current as a function of junction temperature

50

T_j (°C)

0

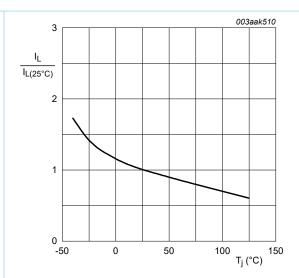
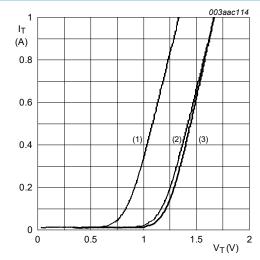


Fig. 8. Normalized latching current as a function of junction temperature

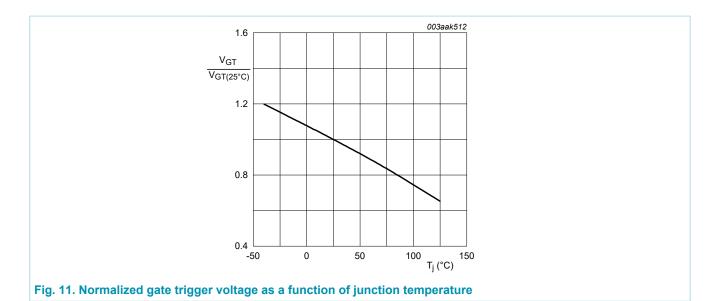


 V_o = 0.835 V; R_s = 0.50 Ω

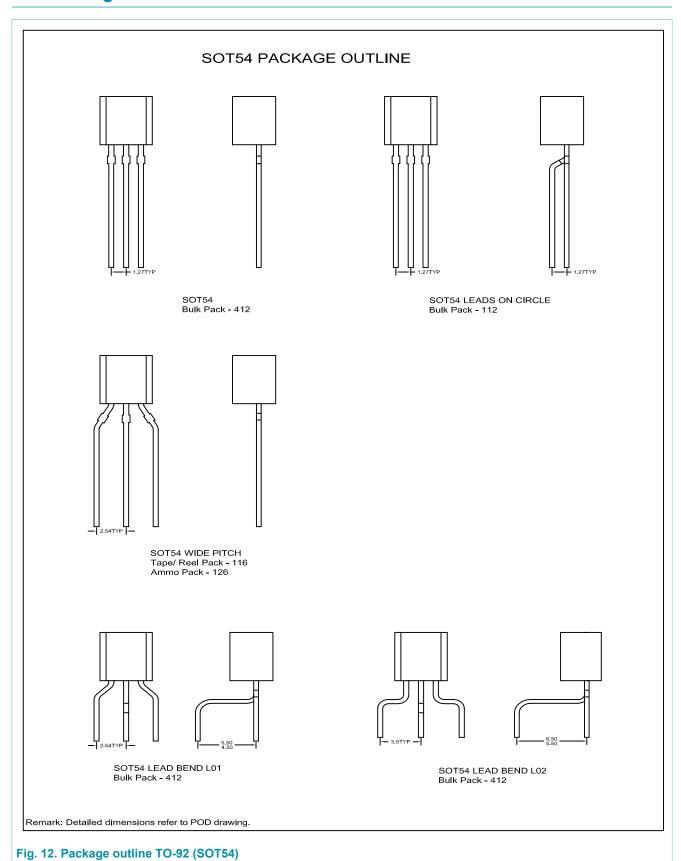
(1) $T_j = 125 \,^{\circ}\text{C}$; typical values (2) $T_j = 125 \,^{\circ}\text{C}$; maximum values (3) $T_j = 25 \,^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

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10. Package outline



BTA2008-800D

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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